

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 09/905,210
Priority Filing Date July 13, 2001
 Inventor Cem Basceri et al.
 Assignee Micron Technology, Inc.
Priority Group Art Unit 1762
Priority Examiner Eric B. Fuller
 Attorney Docket No. MI22-2501
 Customer No. 021567
 Title: Chemical Vapor Deposition Methods of Forming a Barium Strontium
 Titanate Comprising Dielectric Layer Having a Varied Concentration of
 Barium and Strontium With the Layer

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with
 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S.
 patents or U.S. patent application publications are included, as the date of filing
 of this patent application occurs after June 30, 2003. No admission is made
 regarding whether all the listed references are prior art.

Respectfully submitted,

Dated: 1-30-04By: 

Mark S. Matkin
 Reg. No. 32,268

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2501		PRIORITY SERIAL NO. 09/905,320	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Cem Basceri et al.			
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